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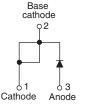
Vishay Semiconductors

# Hyperfast Rectifier, 15 A Fred Pt®





TO-220AC TO-220 FULL-PAK





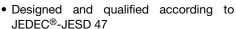
VS-15ETH06PbF VS-15ETH06-N3

VS-15ETH06FPPbF VS-15ETH06FP-N3

PRODUCT SUMMARY					
Package	TO-220AC, TO-220FP				
I <sub>F(AV)</sub>	15 A				
V <sub>R</sub>	600 V				
V <sub>F</sub> at I <sub>F</sub>	1.3 V				
t <sub>rr</sub> typ.	22 ns				
T <sub>J</sub> max.	175 °C				
Diode variation	Single die				

#### **FEATURES**

- Hyperfast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Single die center tap module
- Fully isolated package (V<sub>INS</sub> = 2500 V<sub>RMS</sub>)
- UL E78996 pending



 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>







# HALOGEN FREE Available

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage	$V_{RRM}$		600	V		
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 140 °C	15			
		T <sub>C</sub> = 80 °C (FULL-PAK)	15			
Nico was attained and a comment	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	120	Α		
Non-repetitive peak surge current		T <sub>J</sub> = 25 °C (FULL-PAK)	180			
Peak repetitive forward current	I <sub>FM</sub>		30			
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stq</sub>		-65 to +175	°C		

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	$V_{BR}$ , $V_{R}$	$I_{R} = 100 \mu A$	600	1	-			
Forward voltage	VF	I <sub>F</sub> = 15 A	ı	1.8	2.2	V		
	VF	I <sub>F</sub> = 15 A, T <sub>J</sub> = 150 °C	-	1.3	1.6			
Reverse leakage current	I-	$V_R = V_R$ rated	ı	0.2	50			
neverse leakage current	I <sub>R</sub>	$T_J = 150 ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	30	500	μA		
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	20	-	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 A, dI_F/dt = 100$	$A/\mu s$ , $V_R = 30 V$	1	22	30		
Reverse recovery time		$I_F = 15 \text{ A}, dI_F/dt = 100$	$I_F = 15 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		28	35		
neverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	29	-	ns	
		T <sub>J</sub> = 125 °C	$I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_B = 390 \text{ V}$	-	75	-		
Deal area area area	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	3.5	-	А	
Peak recovery current		T <sub>J</sub> = 125 °C		-	7	-		
Daviawa wasayan dabawa	0	T <sub>J</sub> = 25 °C	.,	-	57	-	nC	
Reverse recovery charge	$Q_{rr}$	T <sub>J</sub> = 125 °C		-	300	-	IIC	
Reverse recovery time	t <sub>rr</sub>		I <sub>E</sub> = 15 A	I <sub>F</sub> = 15 A	-	51	-	ns
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C	dl <sub>F</sub> /dt = 800 A/µs	-	20	-	А	
Reverse recovery charge	Q <sub>rr</sub>		V <sub>R</sub> = 390 V	-	580	-	nC	

THERMAL MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C		
Thermal resistance,	D		-	1.0	1.3			
junction to case (FULL-PAK)	R <sub>thJC</sub>		-	3.0	3.5			
Thermal resistance, junction to ambient per leg	R <sub>thJA</sub>	Typical socket mount	-	-	70	°C/W		
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-			
\M_=:=\L			-	2.0	-	g		
Weight			-	0.07	-	OZ.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Mauldon desides		Case style TO-220AC		15E	ГН06	•		
Marking device		Case style TO-220 FULL-PAK	15ETH06FP					

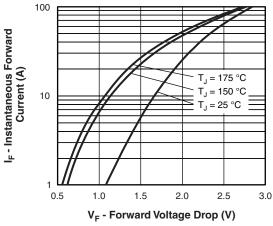


Fig. 1 - Typical Forward Voltage Drop Characteristics

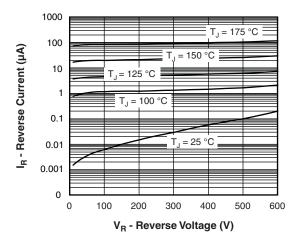


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

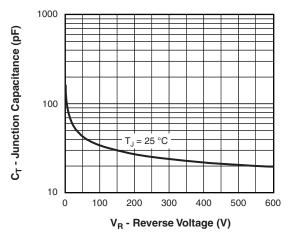


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

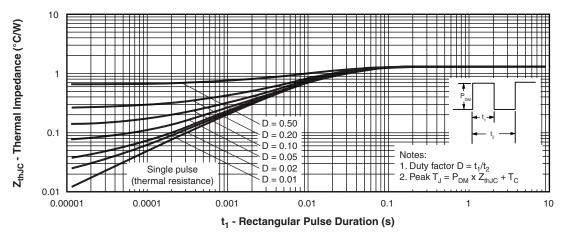


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

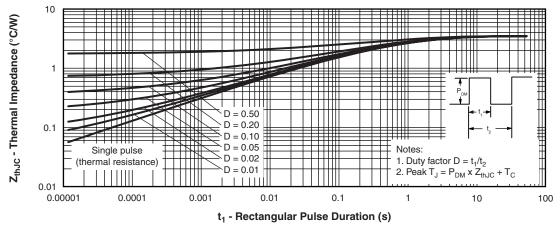


Fig. 5 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics (FULL-PAK)

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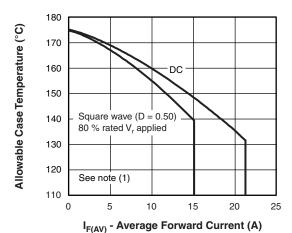


Fig. 6 - Maximum Allowable Case Temperature vs.
Average Forward Current

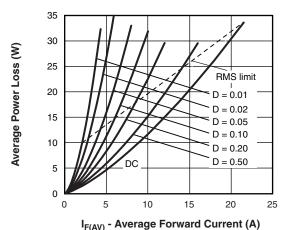


Fig. 8 - Forward Power Loss Characteristics

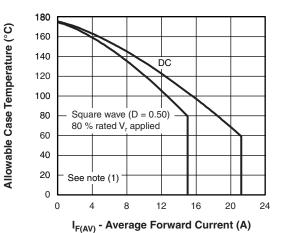


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

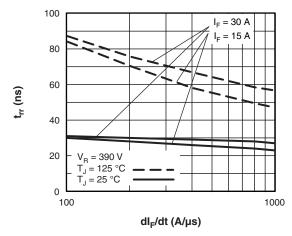


Fig. 9 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

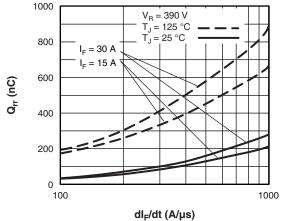


Fig. 10 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 8)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{Rated } V_R \\ \end{array}$ 

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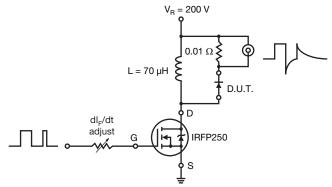
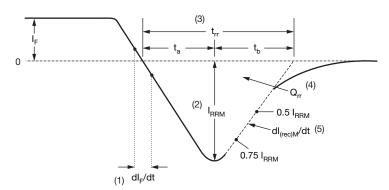


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dI<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RBM</sub> and 0.50 I<sub>RBM</sub> extrapolated to zero current.
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $I_{BBM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

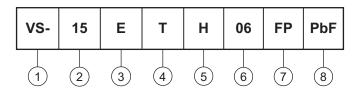
(5) dl<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 12 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

Current rating (15 = 15 A)

3 - E = single diode

**4** - T = TO-220,  $D^2PAK$ 

- H = hyperfast recovery

Voltage rating (06 = 600 V)

7 - • None = TO-220AC

• FP = TO-220 FULL-PAK

8 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

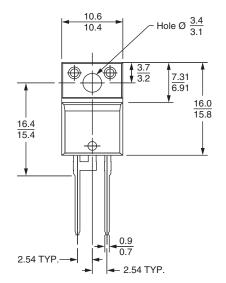
-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

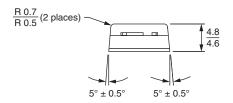
ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-15ETH06PbF	50	1000	Antistatic plastic tube				
VS-15ETH06-N3	50	1000	Antistatic plastic tube				
VS-15ETH06FPPbF	50	1000	Antistatic plastic tube				
VS-15ETH06FP-N3	50	1000	Antistatic plastic tube				

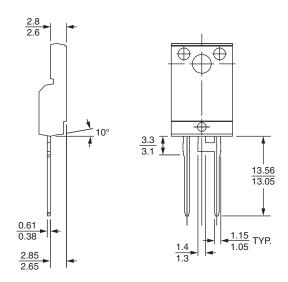
LINKS TO RELATED DOCUMENTS						
Dimensions	TO-220AC	www.vishay.com/doc?95221				
Difficisions	TO-220FP	www.vishay.com/doc?95005				
	TO-220ACPbF	www.vishay.com/doc?95224				
Part marking information	TO-220AC-N3	www.vishay.com/doc?95068				
Part marking information	TO-220FPPbF	www.vishay.com/doc?95009				
	TO-220FP-N3	www.vishay.com/doc?95440				

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#### **DIMENSIONS** in millimeters







#### Lead assignments

**Diodes** 1 + 2 - Cathode

3 - Anode

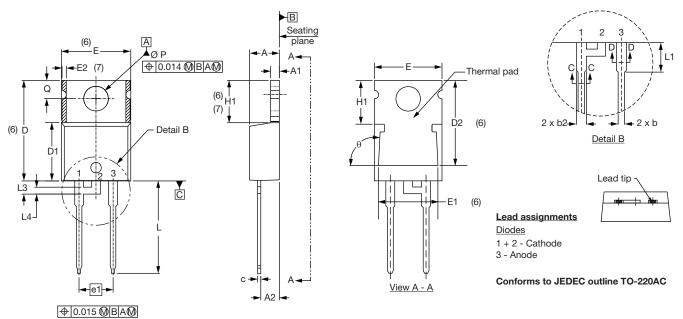
Conforms to JEDEC outline TO-220 FULL-PAK



### Vishay Semiconductors

### **TO-220AC**

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIN	IETERS	INCHES		NOTES
STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6
Е	10.11	10.51	0.398	0.414	3, 6

SYMBOL	MILLIM	IETERS	INCHES		NOTES	
STIMBUL	MIN.	MAX.	MIN.	MAX.	110123	
E1	6.86	8.89	0.270	0.350	6	
E2	-	0.76	-	0.030	7	
е	2.41	2.67	0.095	0.105		
e1	4.88	5.28	0.192	0.208		
H1	6.09	6.48	0.240	0.255	6, 7	
L	13.52	14.02	0.532	0.552		
L1	3.32	3.82	0.131	0.150	2	
L3	1.78	2.13	0.070	0.084		
L4	0.76	1.27	0.030	0.050	2	
ØΡ	3.54	3.73	0.139	0.147		
Q	2.60	3.00	0.102	0.118		
θ	90° t	o 93°	90° to 93°			

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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Revision: 02-Oct-12 Document Number: 91000

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